1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-30092-B.

2. Structure :

2-1. Type : PIN diode.
2-2. Electrodes :
Top side(Anode) : Aluminum alloy.
Back side (Cathode) : Gold.

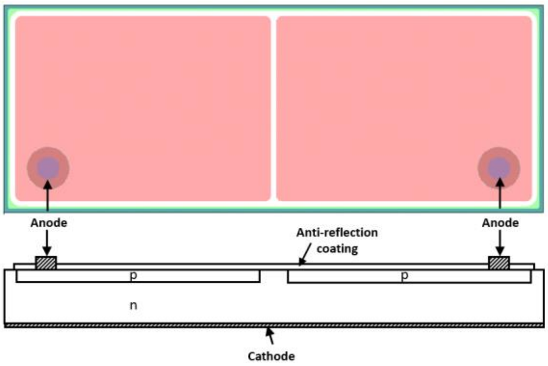
3. Size :

3-1. Chip size (including scribe lane) : 149.6 mils x 57.4 mils (3.8 mm x 1.46 mm).
3-2. Chip thickness : 12 ± 1.0 mils (0.305 ± 0.025 mm).
3-3. Active area : 70.8 mils x 51.1 mils x 2 (1.8 mm x 1.3 mm).
3-4. Bonding pad (Anode) : 11.81 ± 0.394 mils (0.30 ± 0.010 mm) Diameter
3-5. Pattern drawing : Refer to the attached drawing.

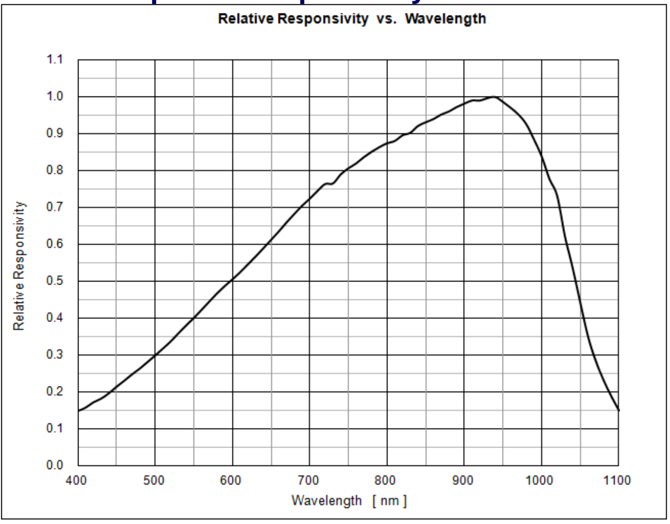
4. Electrical characteristics (Ta = 25 ℃) :

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark current	I_D	V_R=10V Ee=0mW/cm^2			5	nA
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=100uA Ee=0mW/cm^2	60			V
※Forward Voltage	V_F	I_F=10mA Ee=0mW/cm^2			1.3	V
Sensitivity	S	V_R =5V λ =940nm		0.6		A/W

※Based on 100% probing



5. Relative spectral responsivity :



※Bare chip measured with integrating sphere, for reference only.